

### **ABSTRACT**

Bipolar transistors and methods for fabricating bipolar transistors are disclosed wherein an emitter-base dielectric stack is formed between emitter and base structures, comprising a carbide layer situated between first and second oxide layers. The carbide layer provides an etch stop for etching the overlying oxide layer, and the underlying oxide layer provides an etch stop for etching the carbide layer to form an emitter-base contact opening.

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